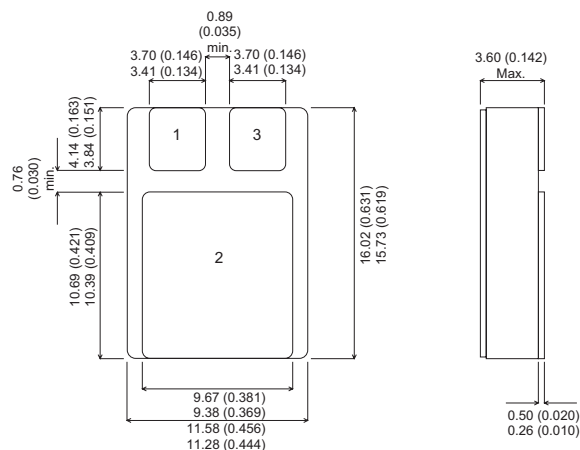


MECHANICAL DATA

Dimensions in mm (inches)



SCHOTTKY DIODE IN HERMETIC CERAMIC SURFACE MOUNT PACKAGE FOR HIGH RELIABILITY APPLICATIONS

PACKAGE SMD1 (TO-267AB)
Underside View

PAD 1 — Anode PAD 2 — Cathode PAD 3 — Not used

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

| | | |
|------------|---|---------------------------|
| V_{RRM} | Repetitive Peak Reverse Voltage | 220V |
| I_{FAV} | Average Forward Current $T_C = 25^\circ\text{C}$ | 12A |
| | $T_C = 90^\circ\text{C}$ | 9A |
| I_{FSM} | Maximum surge forward current $T_{vj} = 45^\circ\text{C}$; $t_p = 10\text{ms}$ (50Hz), sine | 20A |
| T_{vj} | Virtual Junction Temperature | $-55 + 175^\circ\text{C}$ |
| T_{stg} | Storage Temperature Range | $-55 + 150^\circ\text{C}$ |
| P_{tot} | $T_C = 25^\circ\text{C}$ | 78W |
| R_{thjc} | Thermal Characteristics | 3.2°C/W |

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

| Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------------------|--|------|------|------|------|
| I_R^* Reverse Current | $T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ | | | 1.3 | mA |
| | $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$ | | 1.3 | | |
| V_F^* Forward Voltage | $I_F = 5\text{A}$ $T_{VJ} = 125^\circ\text{C}$ | | 1.3 | | V |
| | $I_F = 5\text{A}$ $T_{VJ} = 25^\circ\text{C}$ | 1.2 | | 1.5 | |
| C_J Capacitance | $V_R = 100\text{V}$ $T_{VJ} = 125^\circ\text{C}$ | 18 | | | pF |

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

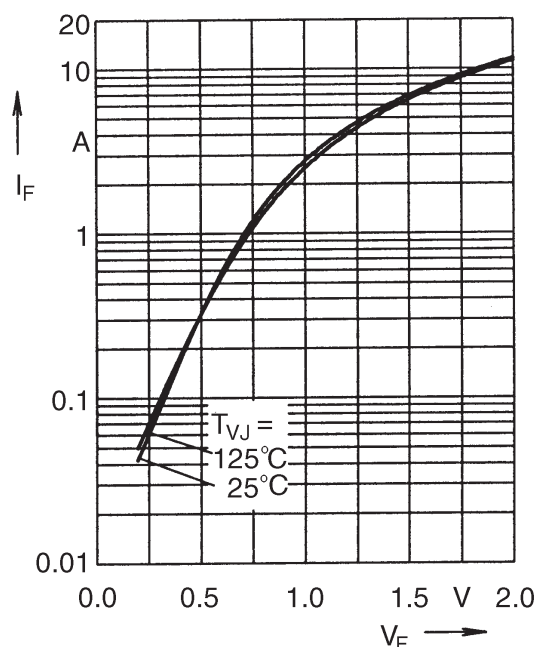


FIG. 1 TYP. FORWARD CHARACTERISTICS

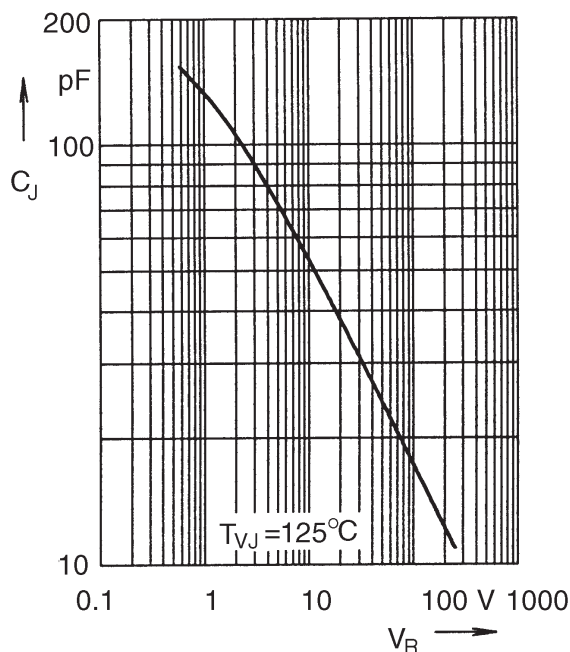


FIG. 2 TYP. JUNCTION CAPACITY VERSUS BLOCKING VOLTAGE

NOTE:

Explanatory comparison for the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes.

| | Rectifier Diode | GaAs Schottky Diodoe |
|--------------------------|--|--|
| Conduction | by majority + minority carriers | by majority carriers only |
| forward characteristics | $V_F(I_F)$ | $V_F(I_F)$, See Fig 1 |
| turn off characteristics | extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr}) | reverse current charges junction capacity C_j , see Fig 2; not temperature dependant |
| turn on characteristics | delayed saturation leads to V_{FR} | no turn on overvoltage peak. |